

Silicon NPN Power Transistors

2SC867

DESCRIPTION

- With TO-66 package
- High collector-base breakdown voltage  
:V<sub>CBO</sub>=400V(min)

APPLICATIONS

- For high voltage and switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

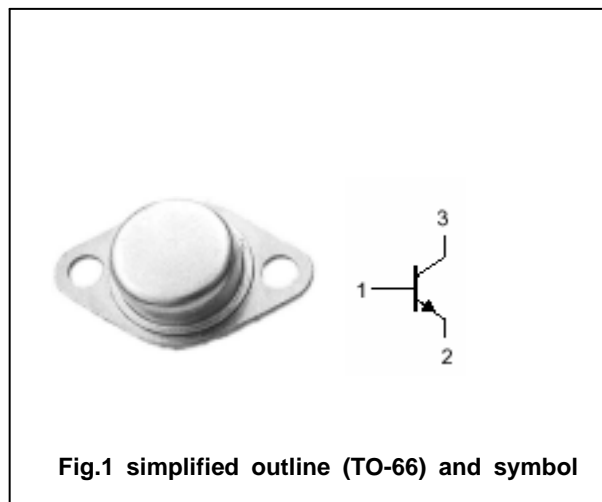


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(T<sub>a</sub>= )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	400	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	150	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		1	A
I <sub>CM</sub>	Collector current-peak		2	A
P <sub>D</sub>	Total power dissipation	T <sub>C</sub> =25	23	W
T <sub>j</sub>	Junction temperature		150	
T <sub>stg</sub>	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =30mA; I <sub>B</sub> =0	150			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =1A; I <sub>B</sub> =0.2 A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =1A; I <sub>B</sub> =0.2 A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =400V; I <sub>E</sub> =0			100	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			100	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.1A ; V <sub>CE</sub> =3V	50			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.2A ; V <sub>CE</sub> =10V		8		MHz

PACKAGE OUTLINE

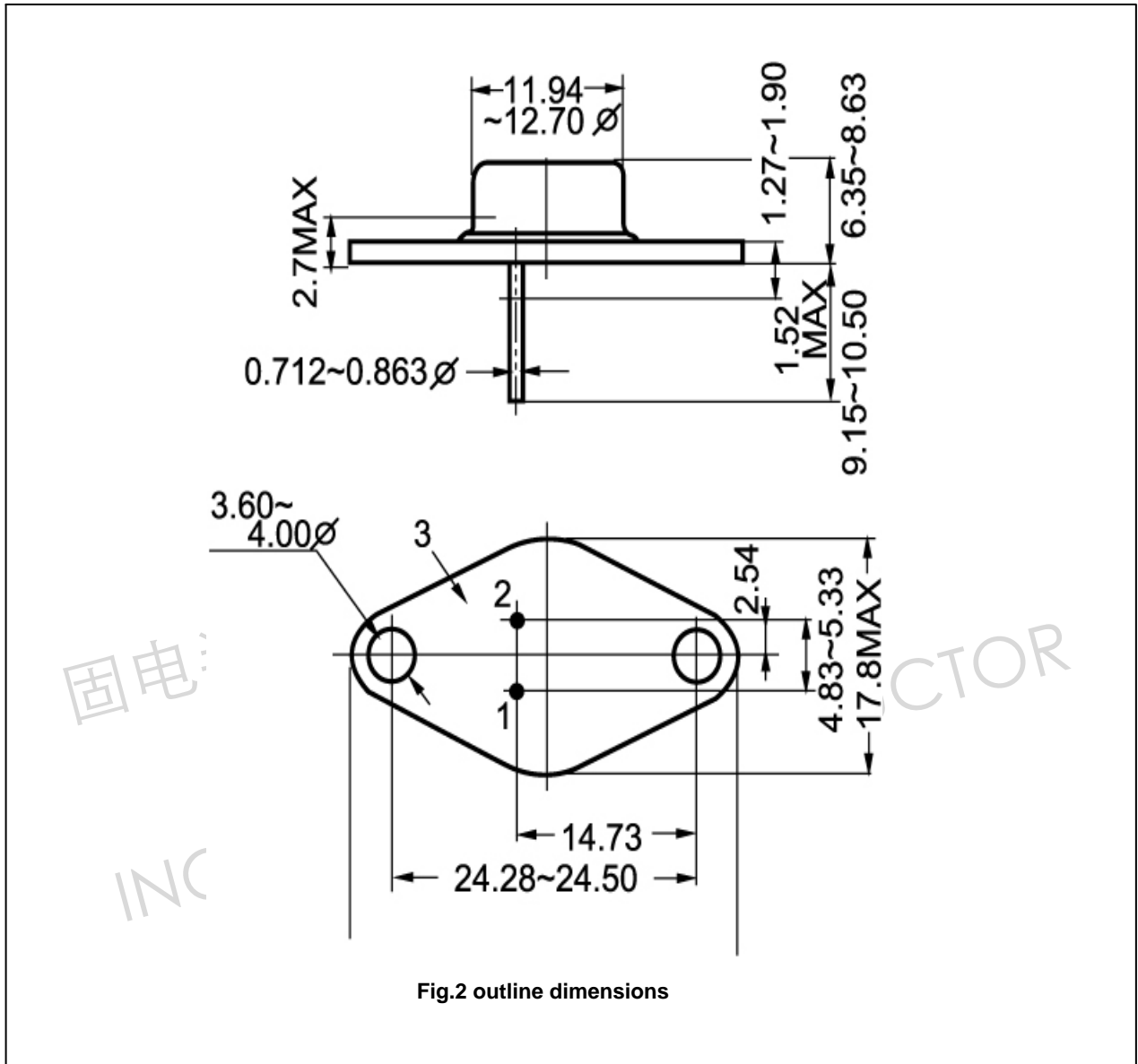


Fig.2 outline dimensions